

ABSTRACT OF THE DISCLOSURE

The present invention provides an MR element bar that permits the fabrication of MR elements in which a variation in characteristics is suppressed, as well as an MR element bar exposure method and formation method enabling the fabrication of the MR element bar. The MR element bar exposure method according to the present invention comprises the steps of: detecting the positions of a plurality of alignment marks  $P_1$  to  $P_4$  formed on a wafer  $W$ ; correcting an exposure position correction region  $R$  on the basis of the positions of detected alignment marks  $P_1'$  to  $P_4'$ ; and exposing a resist which is formed on the wafer  $W$ , wherein an MR element bar region  $B$  comprises a plurality of MR elements (patterns MRE) aligned in the longitudinal direction of the region  $B$ , and one exposure position correction region  $R$  is established for one MR element bar region  $B$ .